

N - CHANNEL ENHANCEMENT MODE " SINGLE FEATURE SIZE™ " POWER MOSFET

TYPE	V _{DSS}	R _{DS(on)}	I _D
STP55NE06L	60 V	< 0.022 Ω	55 A
STP55NE06LFP	60 V	< 0.022 Ω	28 A

- TYPICAL R_{DS(on)} = 0.018 Ω
- EXCEPTIONAL dV/dt CAPABILITY
- 100% AVALANCHE TESTED
- LOW GATE CHARGE 100 °C
- HIGH dV/dt CAPABILITY
- APPLICATION ORIENTED CHARACTERIZATION

DESCRIPTION

This Power Mosfet is the latest development of SGS-THOMSON unique "Single Feature Size" process whereby a single body is implanted on a strip layout structure. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

APPLICATIONS

- DC MOTOR CONTROL
- DC-DC & DC-AC CONVERTERS
- SYNCHRONOUS RECTIFICATION

ABSOLUTE MAXIMUM RATINGS

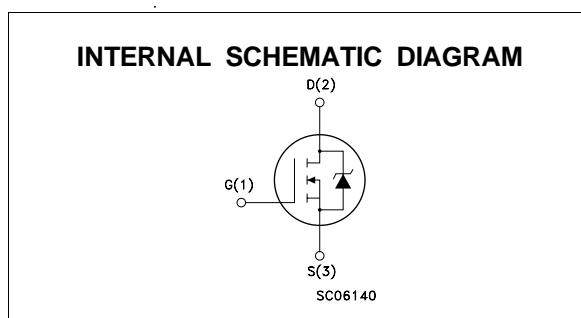
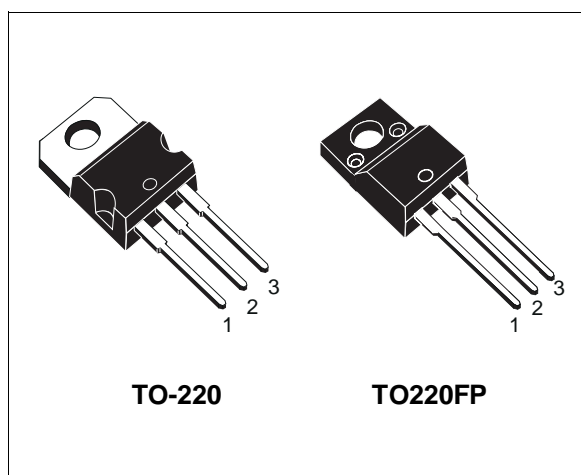
Symbol	Parameter	Value		Unit
		STP55NE06L	STP55NE06LFP	
V _{DS}	Drain-source Voltage (V _{GS} = 0)	60		V
V _{DGR}	Drain- gate Voltage (R _{GS} = 20 kΩ)	60		V
V _{GS}	Gate-source Voltage	± 15		V
I _D	Drain Current (continuous) at T _c = 25 °C	55	28	A
I _D	Drain Current (continuous) at T _c = 100 °C	39	20	A
I _{DM} (•)	Drain Current (pulsed)	220	220	A
P _{tot}	Total Dissipation at T _c = 25 °C	130	35	W
	Derating Factor	0.86	0.23	W/°C
V _{ISO}	Insulation Withstand Voltage (DC)	—	2000	V
dV/dt	Peak Diode Recovery voltage slope	7		V/ns
T _{stg}	Storage Temperature	-65 to 175		°C
T _j	Max. Operating Junction Temperature	175		°C

(•) Pulse width limited by safe operating area

(1) I_{SD} ≤ 55 A, di/dt ≤ 300 A/μs, V_{DD} ≤ V_{(BR)DSS}, T_j ≤ T_{JMAX}

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STP55NE06LFP

THERMAL DATA

			TO-220	TO-220FP	
R _{thj-case}	Thermal Resistance Junction-case	Max	1.15	4.28	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	62.5		°C/W
R _{thc-sink}	Thermal Resistance Case-sink	Typ	0.5		°C/W
T _l	Maximum Lead Temperature For Soldering Purpose		300		°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I _{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T _j max, δ < 1%)	55	A
E _{AS}	Single Pulse Avalanche Energy (starting T _j = 25 °C, I _D = I _{AR} , V _{DD} = 25 V)	250	mJ

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 μA V _{GS} = 0	60			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating T _c = 125 °C			1 10	μA μA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ± 15 V			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} I _D = 250 μA	1	1.7	2.5	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 5 V I _D = 27.5 A V _{GS} = 10 V I _D = 27.5 A		0.022 0.019	0.028 0.022	Ω
I _{D(on)}	On State Drain Current	V _{DS} > I _{D(on)} × R _{DS(on)max} V _{GS} = 10 V	55			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (*)	Forward Transconductance	V _{DS} > I _{D(on)} × R _{DS(on)max} I _D = 27.5 A	20	30		S
C _{iss}	Input Capacitance	V _{DS} = 25 V f = 1 MHz V _{GS} = 0		2800	3750	pF
C _{oss}	Output Capacitance			375	500	pF
C _{rss}	Reverse Transfer Capacitance			100	140	pF

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Time	$V_{DD} = 30\text{ V}$ $I_D = 27.5\text{ A}$		40	55	ns
t_r	Rise Time	$R_G = 4.7\ \Omega$ $V_{GS} = 5\text{ V}$		100	140	ns
Q_g	Total Gate Charge	$V_{DD} = 48\text{ V}$ $I_D = 55\text{ A}$ $V_{GS} = 5\text{ V}$		40	55	nC
Q_{gs}	Gate-Source Charge			13		nC
Q_{gd}	Gate-Drain Charge			20		nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(voff)}$	Off-voltage Rise Time	$V_{DD} = 48\text{ V}$ $I_D = 55\text{ A}$		25	35	ns
t_f	Fall Time	$R_G = 4.7\ \Omega$ $V_{GS} = 5\text{ V}$		40	55	ns
t_c	Cross-over Time			65	90	ns

SOURCE DRAIN DIODE

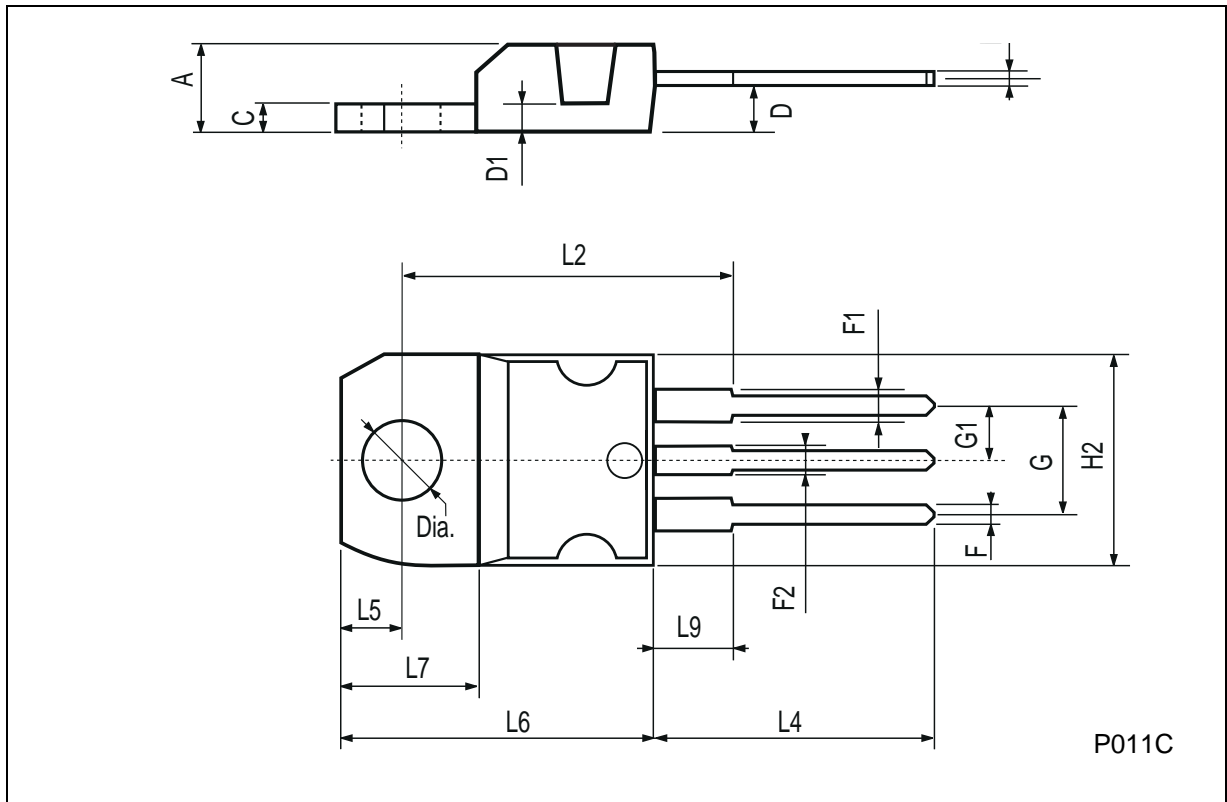
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				55	A
$I_{SDM}(\bullet)$	Source-drain Current (pulsed)				220	A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 55\text{ A}$ $V_{GS} = 0$			1.5	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 55\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 30\text{ V}$ $T_j = 150\text{ }^\circ\text{C}$		65		ns
Q_{rr}	Reverse Recovery Charge			180		nC
I_{RRM}	Reverse Recovery Current			5.5		A

(*) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

(\bullet) Pulse width limited by safe operating area

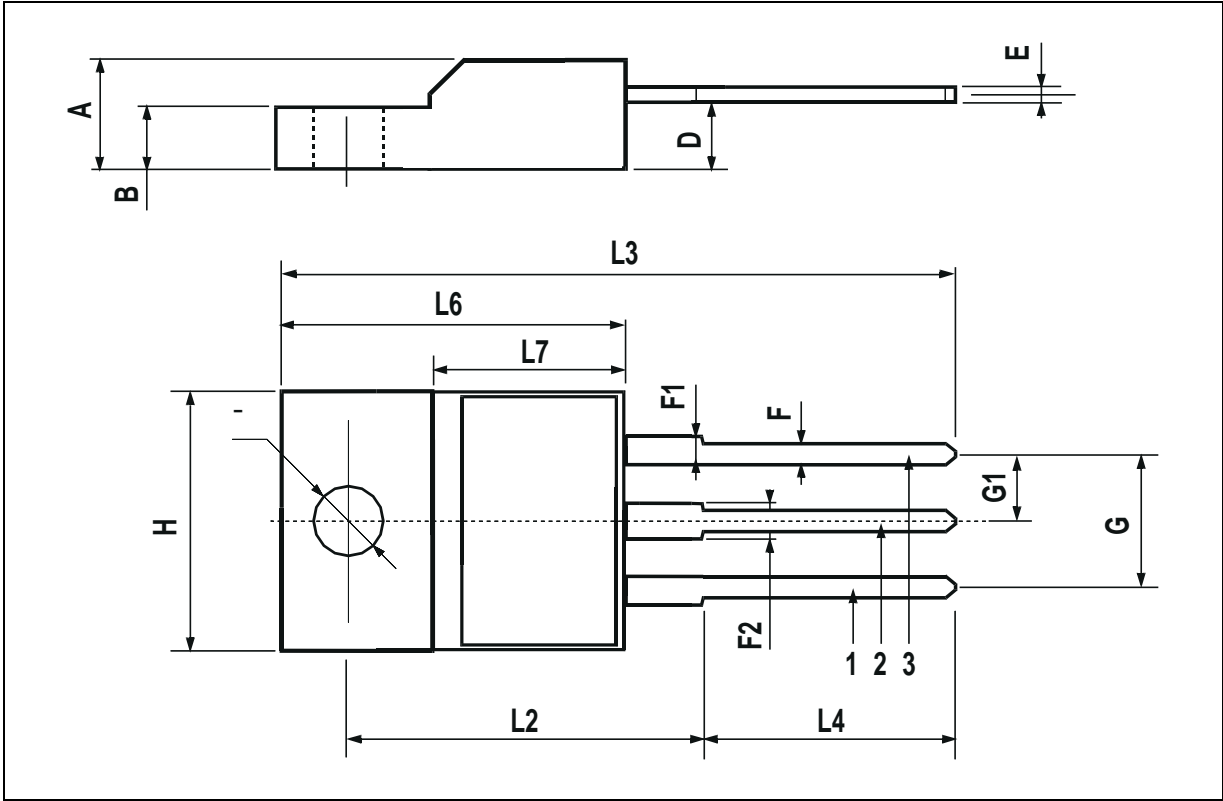
TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



TO-220FP MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	0.385		0.417
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



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